

TOSHIBA PHOTOTRANSISTOR SILICON NPN EPITAXIAL PLANAR

TPS604

PHOTO TRANSISTOR FOR PHOTO SENSOR

PHOTOELECTRIC COUNTER

VARIOUS KINDS OF READERS

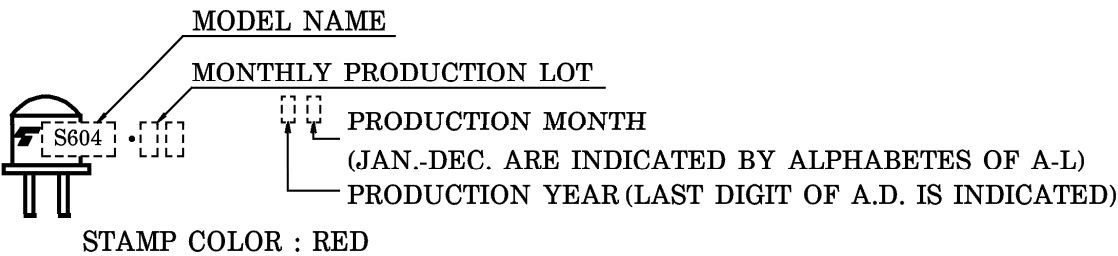
POSITION DETECTION

- TO-18 metal package
- High sensitivity.
- Sharp directivity. Incident light can be effectively used.
: $\theta_{\frac{1}{2}} = \pm 10^\circ$ (Typ.)
- Countermeasure against disturbance light, improvement of response speed and enable operation can be taken by use of the base pin. Avoid the use of TPS604 with the base pin kept open.
- The same size TPS601A with the base pin is available.

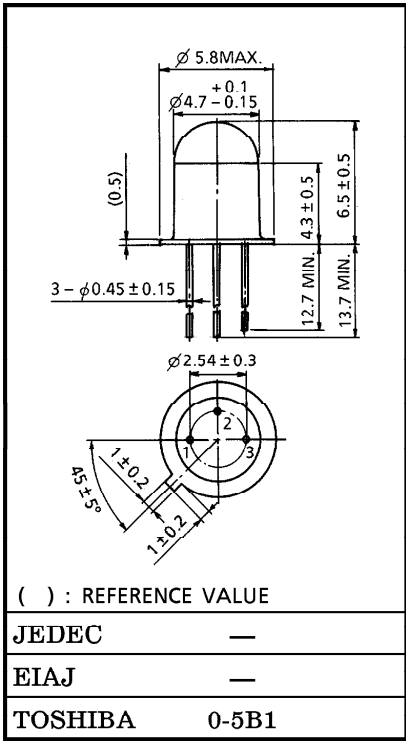
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V _{CEO}	40	V
Collector-Base Voltage	V _{CBO}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Emitter-Collector Voltage	V _{ECO}	5	V
Collector Current	I _C	50	mA
Collector Power Dissipation	P _C	150	mW
Collector Power Dissipation Derating (Ta > 25°C)	$\Delta P_C / ^\circ C$	-1.2	mW / °C
Operating Temperature Range	T _{opr}	-40~125	°C
Storage Temperature Range	T _{stg}	-55~150	°C

PRODUCT INDICATION



Unit in mm



() : REFERENCE VALUE

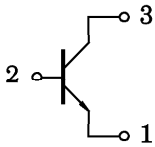
JEDEC —

EIAJ —

TOSHIBA 0-5B1

Weight : 0.37g (Typ.)

PIN CONNECTION



1. EMITTER
2. BASE
3. COLLECTOR (CASE)

961001EAA2

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OPTO-ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Dark Current		$I_D (I_{CEO})$	$V_{CE} = 30V, E = 0$	—	0.01	0.2	μA
Light Current		I_L	$V_{CE} = 3V, E = 0.1mW / cm^2$ (Note)	60	200	—	μA
Collector-Emitter Saturation Voltage		$V_{CE (sat)}$	$I_C = 30\mu A, E = 0.1mW / cm^2$ (Note)	—	0.25	0.4	V
Switching Time	Rise Time	t_r	$V_{CC} = 10V, I_C = 10mA$ $R_L = 100\Omega$	—	2	—	μs
	Fall Time	t_f		—	2	—	
Peak Sensitivity Wavelength		λ_P	—	—	800	—	nm
Half Value Angle		$\theta \frac{1}{2}$	—	—	± 10	—	°

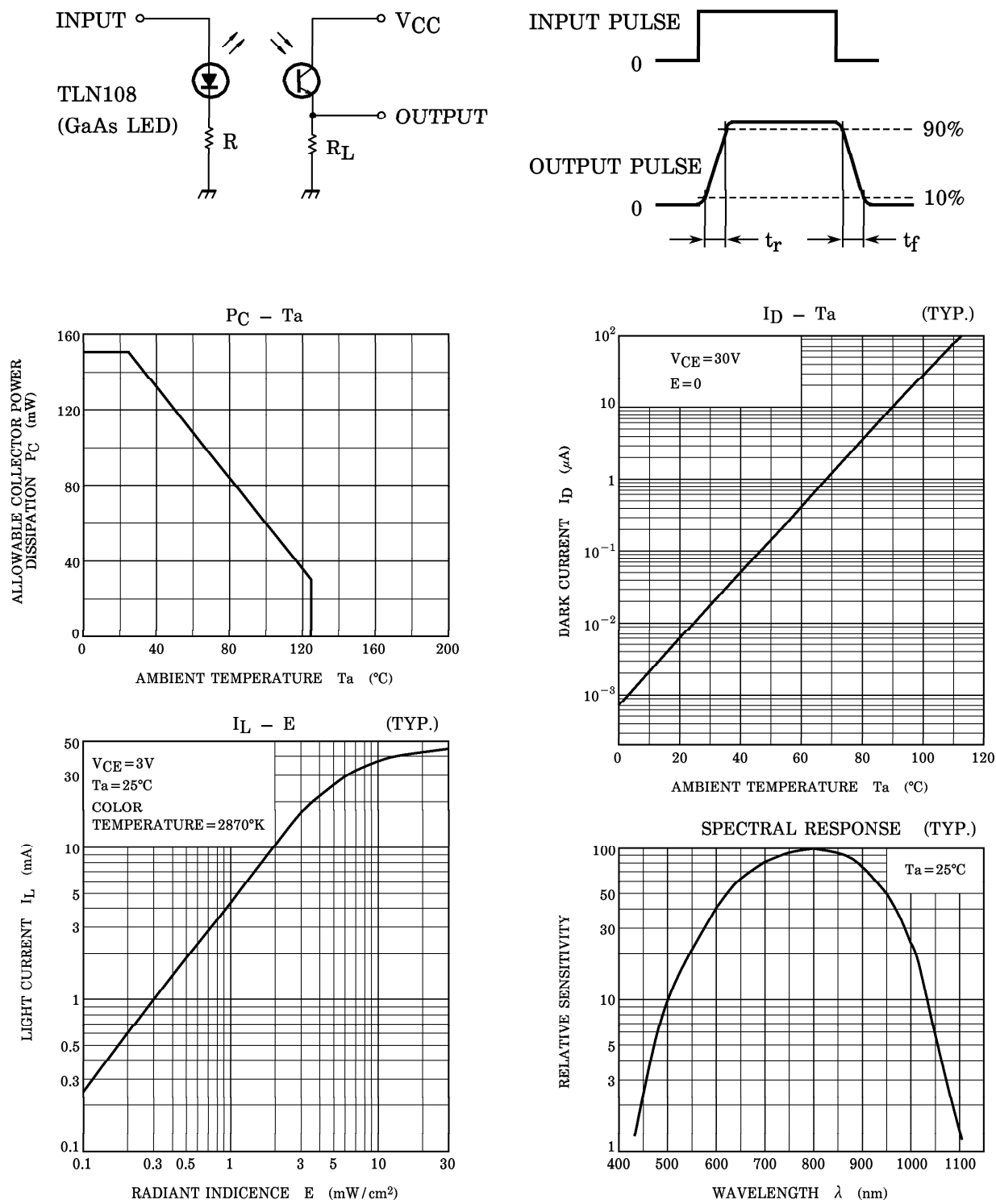
Note : Color temperature = 2870°K, Standard Tungsten Lamp

PRECAUTION

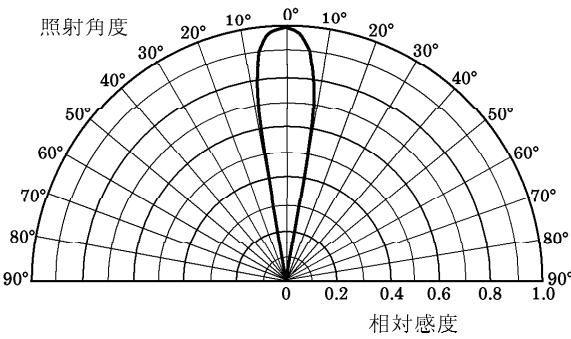
Please be careful of the followings.

1. Soldering temperature : 260°C MAX.
Soldering time : 5s MAX.
(Soldering portion of lead : above 1.5mm from the body of the device)
2. If the lead is formed, the lead should be formed at a distance of 2mm from the body of the device.
Soldering shall be performed after lead forming.

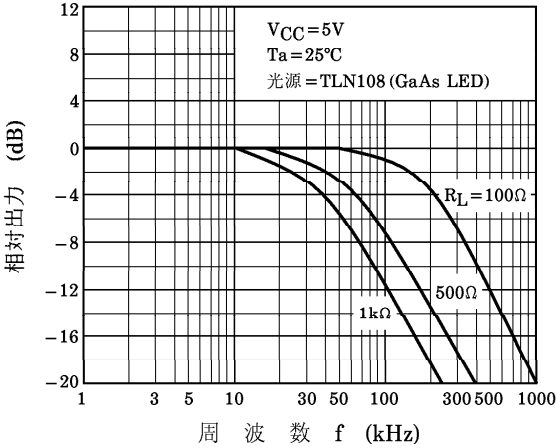
Fig.1 SWITCHING TIME TEST CIRCUIT



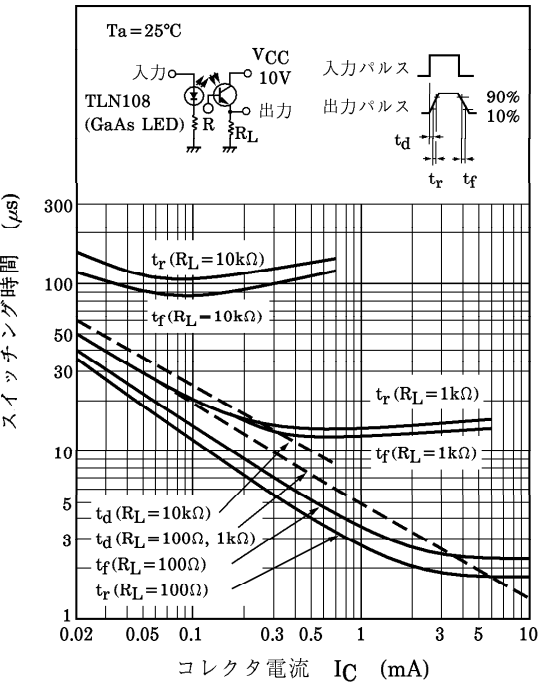
指向感度特性 (標準値)
(Ta = 25°C)



周波数特性 (標準値)



スイッチング特性 (標準値)



TLN108との結合特性

